

FGD3245G2-F085C

EcoSPARK[®] 2 Ignition IGBT

320 mJ, 450 V, N-Channel Ignition IGBT

Features

- SCIS Energy = 320 mJ at $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- Low Saturation Voltage
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Automotive Ignition Coil Driver Circuits
- High Current Ignition System
- Coil on Plug Application

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
BV_{CER}	Collector to Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)	450	V
BV_{ECS}	Emitter to Collector Voltage – Reverse Battery Condition ($I_C = 10\text{ mA}$)	28	V
E_{SCIS25}	ISCIS = 14.6 A, L = 3.0 mHy, RGE = 1 K Ω , $T_C = 25^\circ\text{C}$ (Note 1)	320	mJ
$E_{SCIS150}$	ISCIS = 10.9 A, L = 3.0 mHy, RGE = 1 K Ω , $T_C = 150^\circ\text{C}$ (Note 2)	180	mJ
IC25	Collector Current Continuous at $V_{GE} = 4.0\text{ V}$, $T_C = 25^\circ\text{C}$	23	A
IC110	Collector Current Continuous at $V_{GE} = 4.0\text{ V}$, $T_C = 110^\circ\text{C}$	23	A
V_{GEM}	Gate to Emitter Voltage Continuous	± 10	V
PD	Power Dissipation Total, $T_C = 25^\circ\text{C}$	150	W
	Power Dissipation Derating, $T_C > 25^\circ\text{C}$	1.1	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	300	$^\circ\text{C}$
T_{PKG}	Reflow Soldering according to JESD020C	260	$^\circ\text{C}$
ESD	HBM–Electrostatic Discharge Voltage at 100 pF, 1500 Ω	4	kV
	CDM–Electrostatic Discharge Voltage at 1 Ω	2	kV

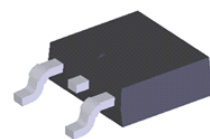
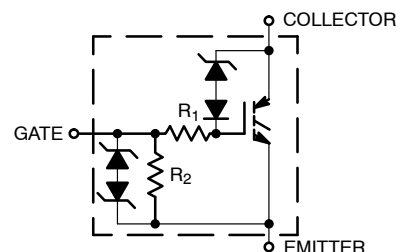
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Self clamped inductive Switching Energy (E_{SCIS25}) of 320 mJ is based on the test conditions that is starting $T_J = 25^\circ\text{C}$, L = 3 mHy, ISCIS = 14.6 A, VCC = 100 V during inductor charging and VCC = 0 V during time in clamp.
2. Self Clamped inductive Switching Energy ($E_{SCIS150}$) of 180 mJ is based on the test conditions that is starting $T_J = 150^\circ\text{C}$, L = 3mHy, ISCIS = 10.9 A, VCC = 100 V during inductor charging and VCC = 0 V during time in clamp.



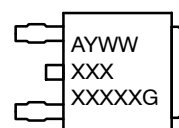
ON Semiconductor[®]

www.onsemi.com



DPAK3
CASE 369AS

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- XXXX = Device Code
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FGD3245G2-F085C

THERMAL RESISTANCE RATINGS

Characteristic	Symbol	Max	Units
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	0.9	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
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OFF CHARACTERISTICS

BV_{CER}	Collector to Emitter Breakdown Voltage	$I_{CE} = 2\text{ mA}, V_{GE} = 0\text{ V},$ $R_{GE} = 1\text{ k}\Omega,$ $T_J = -40\text{ to }150^\circ\text{C}$	420	-	480	V	
BV_{CES}	Collector to Emitter Breakdown Voltage	$I_{CE} = 10\text{ mA}, V_{GE} = 0\text{ V},$ $R_{GE} = 0,$ $T_J = -40\text{ to }150^\circ\text{C}$	440	-	500	V	
BV_{ECS}	Emitter to Collector Breakdown Voltage	$I_{CE} = -75\text{ mA}, V_{GE} = 0\text{ V},$ $T_J = 25^\circ\text{C}$	28	-	-	V	
BV_{GES}	Gate to Emitter Breakdown Voltage	$I_{GES} = \pm 2\text{ mA}$	± 12	± 14	-	V	
I_{CER}	Collector to Emitter Leakage Current	$V_{CE} = 175\text{ V}$ $R_{GE} = 1\text{ k}\Omega$	$T_J = 25^\circ\text{C}$	-	-	25	μA
			$T_J = 150^\circ\text{C}$	-	-	1	mA
I_{ECS}	Emitter to Collector Leakage Current	$V_{EC} = 24\text{ V}$	$T_J = 25^\circ\text{C}$	-	-	1	mA
			$T_J = 150^\circ\text{C}$	-	-	40	
R_1	Series Gate Resistance		-	120	-	Ω	
R_2	Gate to Emitter Resistance		10K	-	30K	Ω	

ON CHARACTERISTICS

$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_{CE} = 6\text{ A}, V_{GE} = 4\text{ V}, T_J = 25^\circ\text{C}$	-	1.13	1.25	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_{CE} = 10\text{ A}, V_{GE} = 4.5\text{ V}, T_J = 150^\circ\text{C}$	-	1.32	1.50	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_{CE} = 15\text{ A}, V_{GE} = 5\text{ V}, T_J = 150^\circ\text{C}$	-	1.64	1.85	V

DYNAMIC CHARACTERISTICS

$Q_{G(ON)}$	Gate Charge	$I_{CE} = 10\text{ A}, V_{CE} = 12\text{ V}, V_{GE} = 5\text{ V}$	-	23	-	nC	
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	$I_{CE} = 1\text{ mA}$ $V_{CE} = V_{GE}$	$T_J = 25^\circ\text{C}$	1.3	1.6	2.2	V
			$T_J = 150^\circ\text{C}$	0.75	1.1	1.8	
V_{GEP}	Gate to Emitter Plateau Voltage	$V_{CE} = 12\text{ V}, I_{CE} = 10\text{ A}$	-	2.7	-	V	

SWITCHING CHARACTERISTICS

$td_{(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14\text{ V}, R_L = 1\text{ }\Omega,$ $V_{GE} = 5\text{ V}, R_G = 470\text{ }\Omega,$ $T_J = 25^\circ\text{C}$	-	0.9	4	μs
t_{rR}	Current Rise Time-Resistive		-	2.6	7	
$td_{(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300\text{ V}, L = 1\text{ mH},$ $V_{GE} = 5\text{ V}, R_G = 470\text{ }\Omega,$ $I_{CE} = 6.5\text{ A}, T_J = 25^\circ\text{C}$	-	5.4	15	
t_{fL}	Current Fall Time-Inductive		-	2.7	15	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Device	Package	Shipping [†]
FGD3245G2-F085C	DPAK (Pb-Free)	2500 Units/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

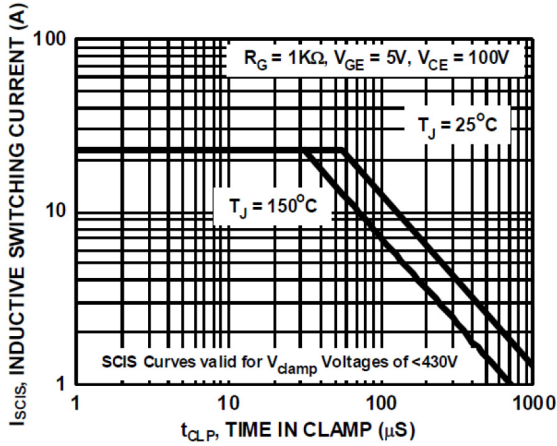


Figure 1. Self Clamped Inductive Switching Current vs. Time in Clamp

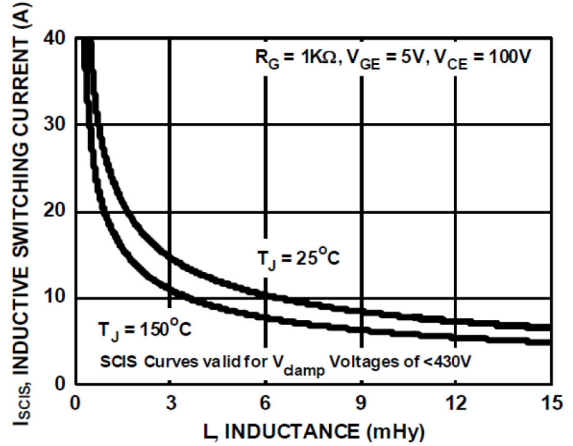


Figure 2. Self Clamped Inductive Switching Current vs. Inductance

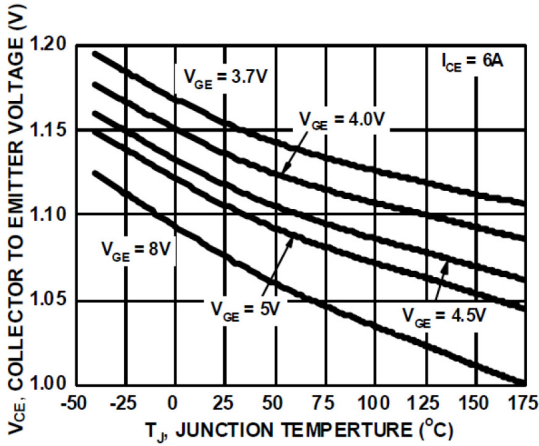


Figure 3. Collector to Emitter On-State Voltage vs. Junction Temperature

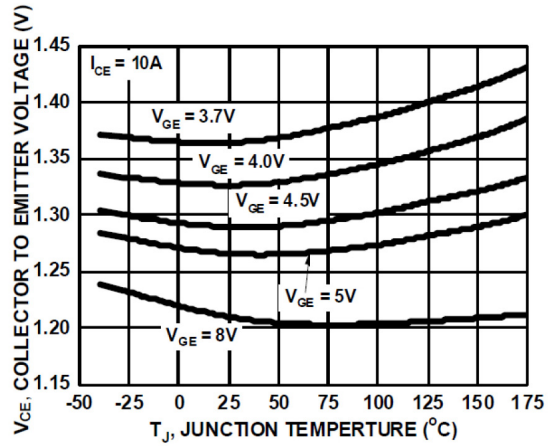


Figure 4. Collector to Emitter On-State Voltage vs. Junction Temperature

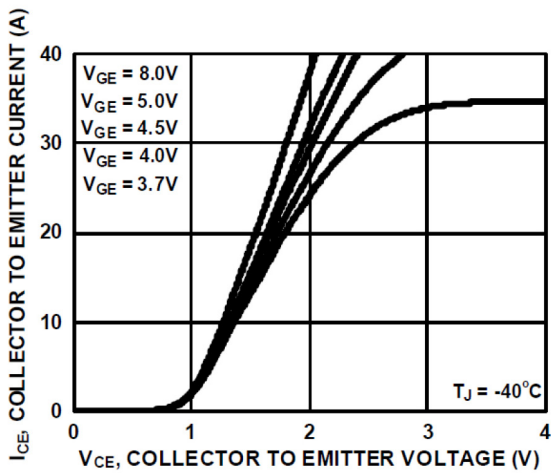


Figure 5. Collector to Emitter On-State Voltage vs. Collector Current

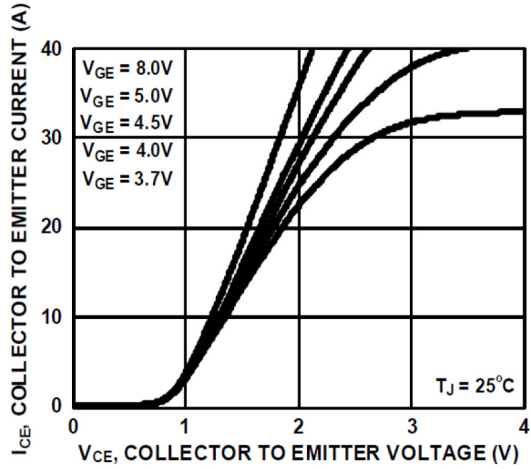


Figure 6. Collector to Emitter On-State Voltage vs. Collector Current

TYPICAL CHARACTERISTICS (continued)

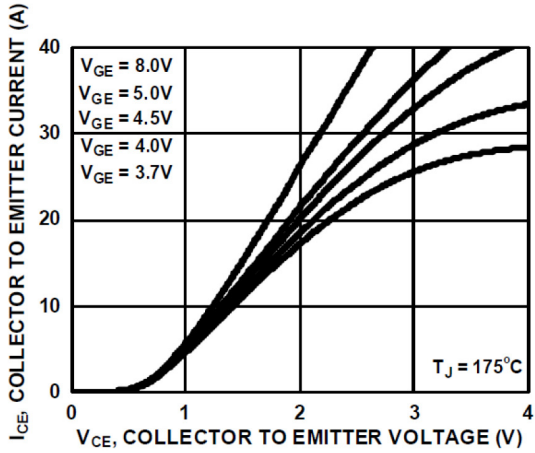


Figure 7. Collector to Emitter On-State Voltage vs. Collector Current

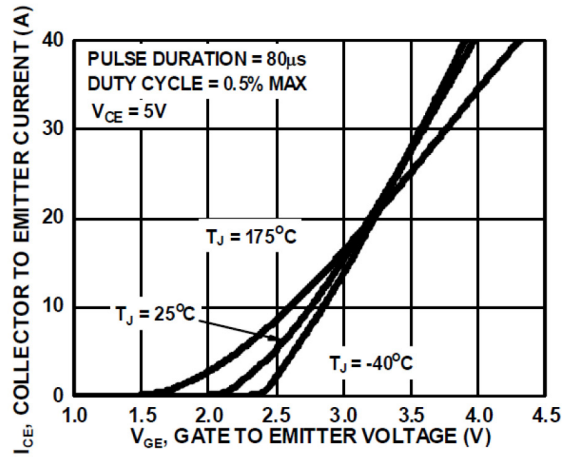


Figure 8. Transfer Characteristics

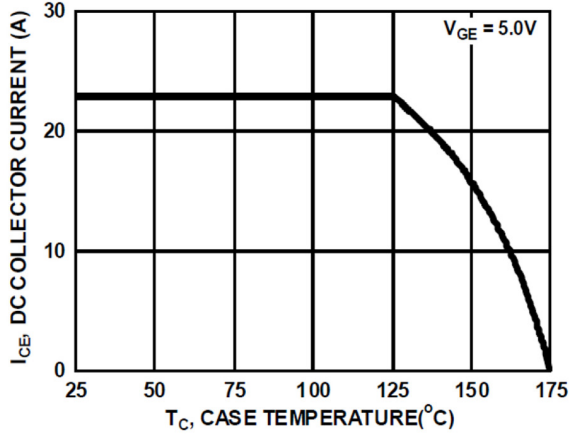


Figure 9. DC Collector Current vs. Case Temperature

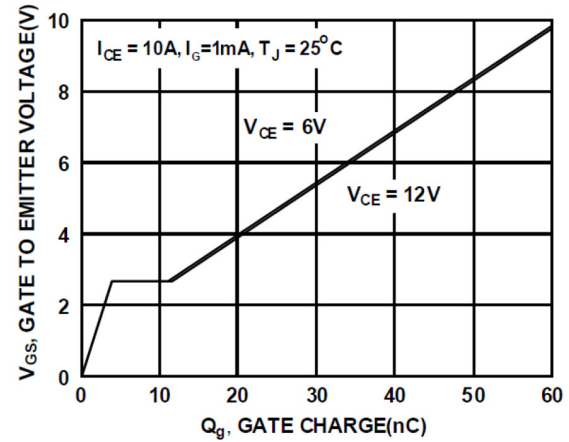


Figure 10. Gate Charge

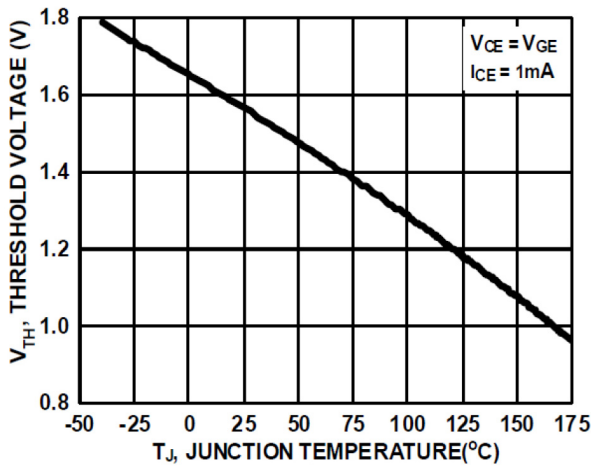


Figure 11. Threshold Voltage vs. Junction Temperature

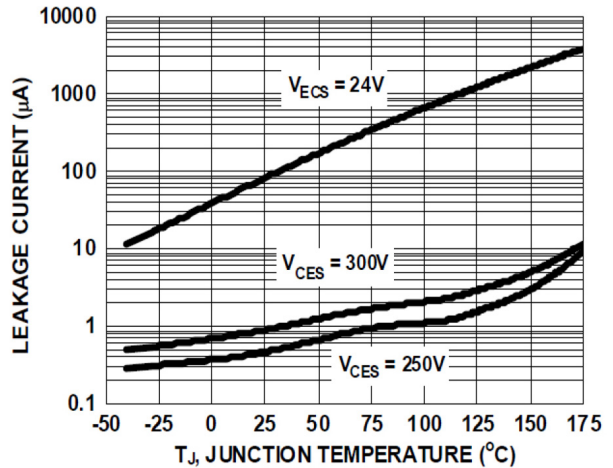


Figure 12. Leakage Current vs. Junction Temperature

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TYPICAL CHARACTERISTICS (continued)

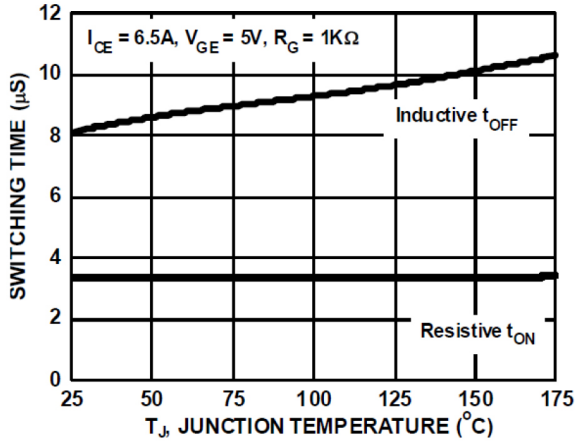


Figure 13. Switching Time vs. Junction Temperature

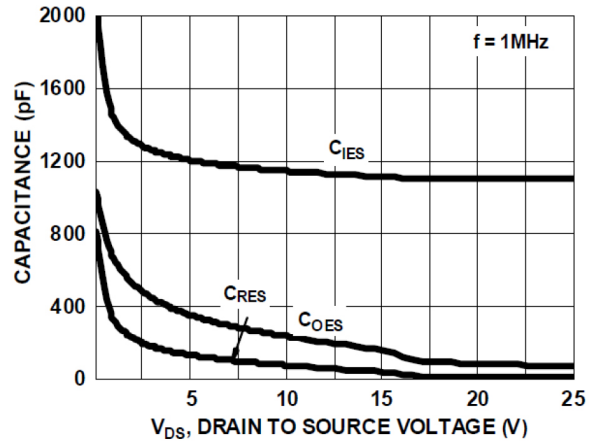


Figure 14. Capacitance vs. Collector to Emitter

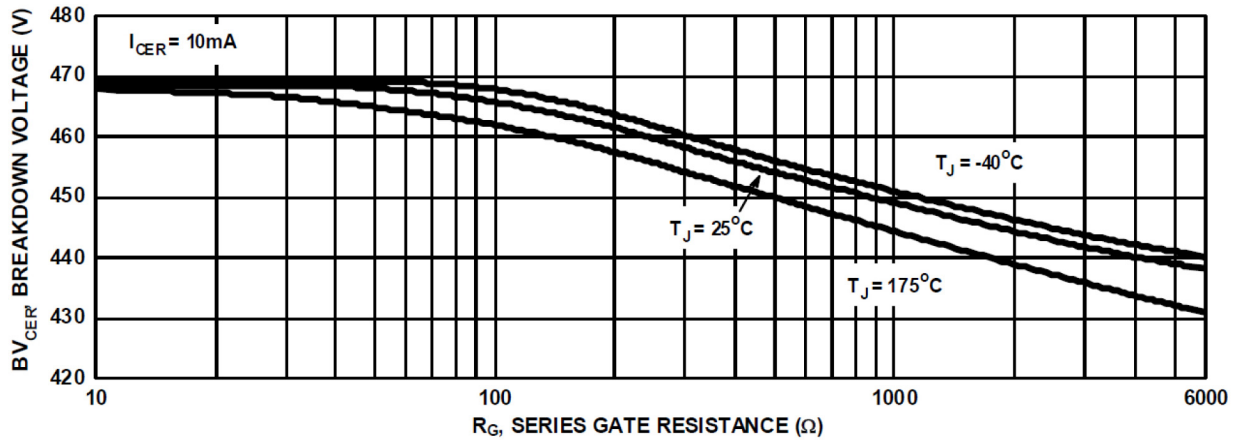


Figure 15. Break Down Voltage vs. Series Resistance

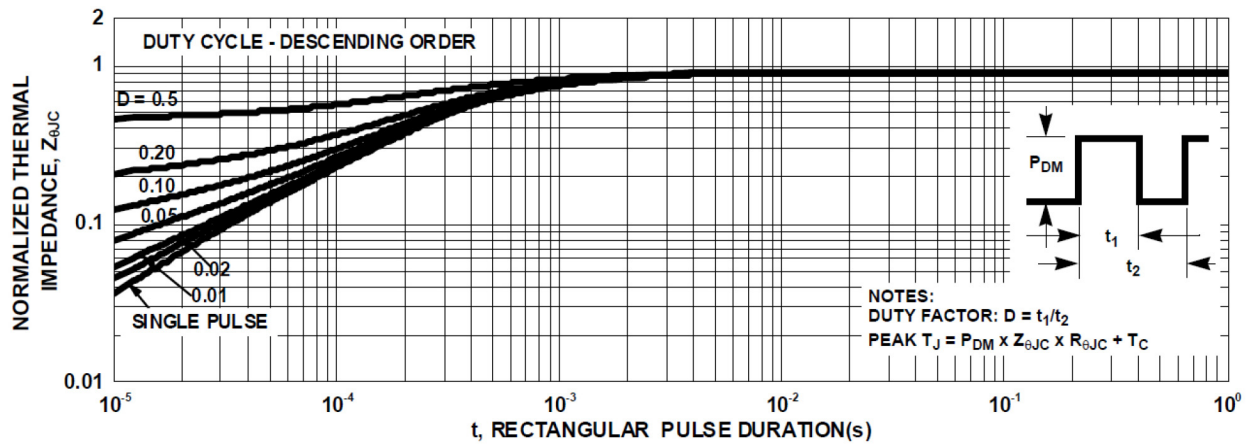


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

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TEST CIRCUIT AND WAVEFORMS

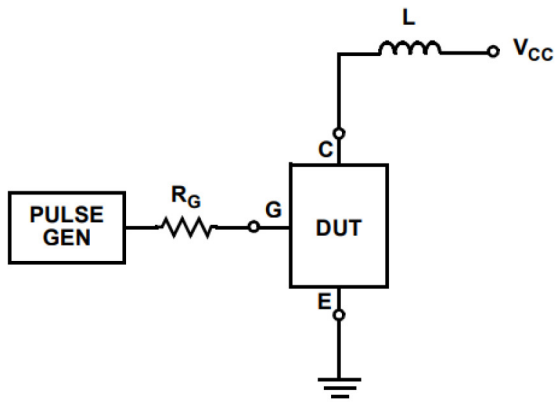


Figure 17. Inductive Switching Test Circuit

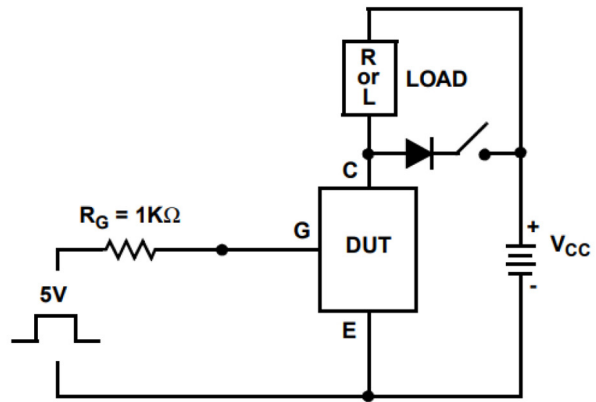


Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

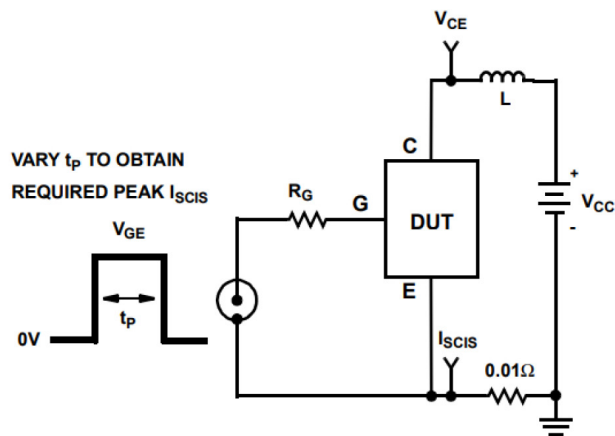


Figure 19. Energy Test Circuit

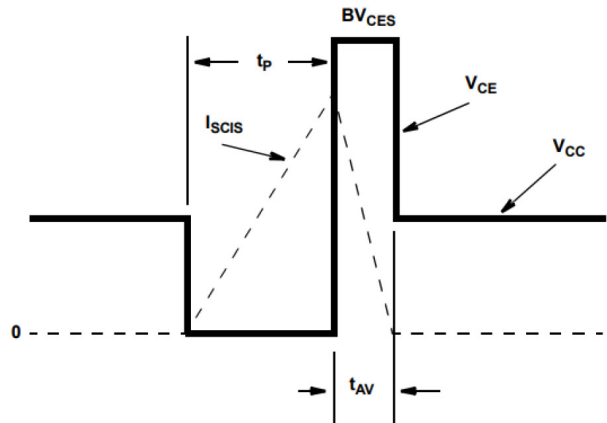


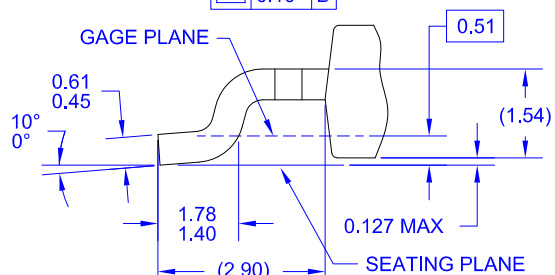
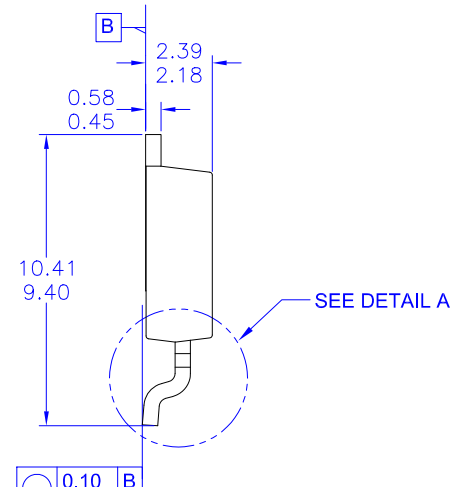
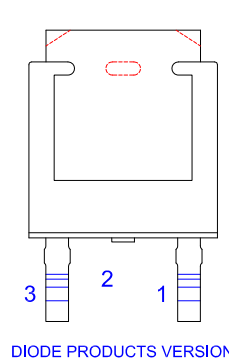
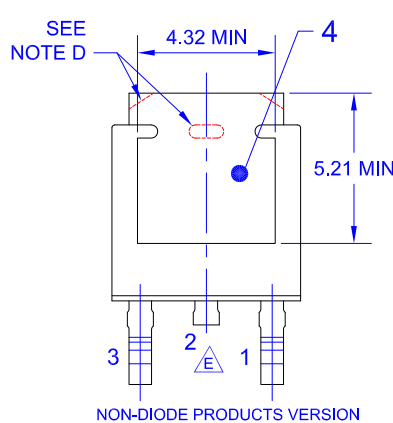
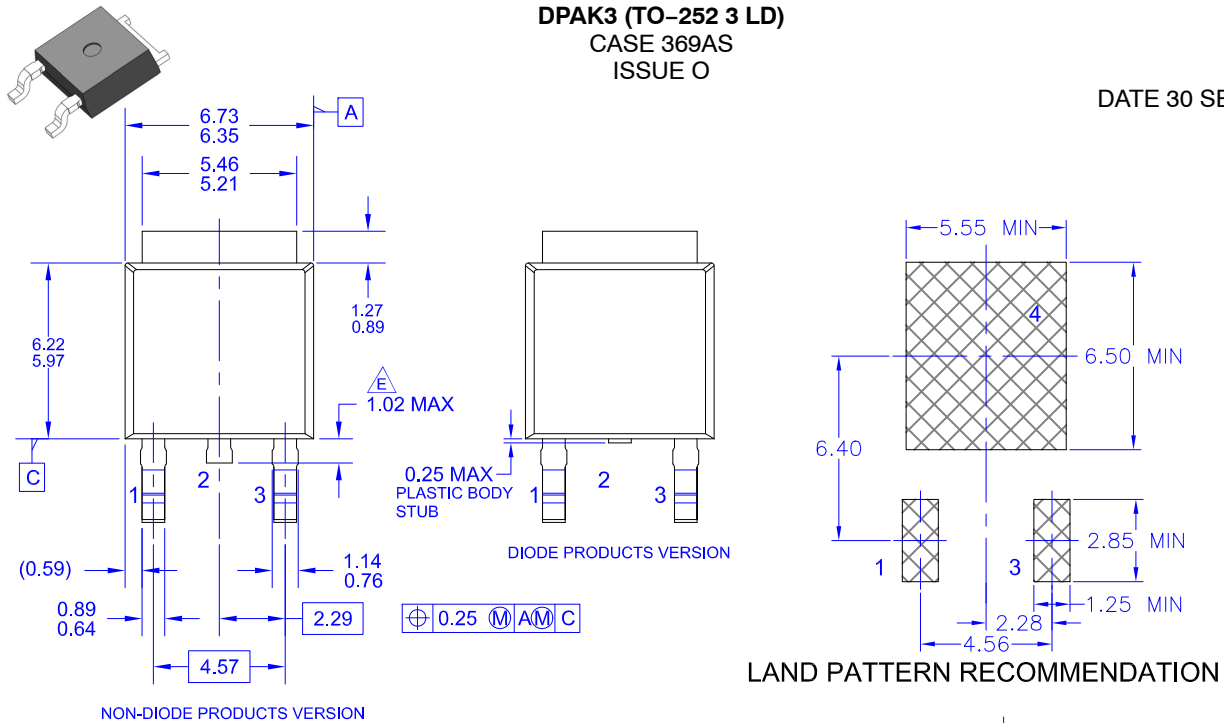
Figure 20. Energy Waveforms

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



DPAK3 (TO-252 3 LD) CASE 369AS ISSUE O

DATE 30 SEP 2016



DETAIL A
(ROTATED -90°)
SCALE: 12X

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
 - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

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DESCRIPTION:	DPAK3 (TO-252 3 LD)	PAGE 1 OF 1

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